

# 2SC5739

## Silicon NPN epitaxial planar type

Power supply for Audio & Visual equipments

such as TVs and VCRs

Industrial equipments such as DC-DC converters

### ■ Features

- High-speed switching ( $t_{stg}$ : storage time/ $t_f$ : fall time is short)
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Superior forward current transfer ratio  $h_{FE}$  linearity
- TO-220D built-in: Excellent package with withstand voltage 5 kV guaranteed

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

| Parameter                             | Symbol    | Rating                   | Unit             |
|---------------------------------------|-----------|--------------------------|------------------|
| Collector-base voltage (Emitter open) | $V_{CBO}$ | 60                       | V                |
| Collector-emitter voltage (Base open) | $V_{CEO}$ | 60                       | V                |
| Emitter-base voltage (Collector open) | $V_{EBO}$ | 6                        | V                |
| Collector current                     | $I_C$     | 3                        | A                |
| Peak collector current *              | $I_{CP}$  | 6                        | A                |
| Collector power dissipation           | $P_C$     | 20                       | W                |
|                                       |           | $T_a = 25^\circ\text{C}$ |                  |
| Junction temperature                  | $T_j$     | 150                      | $^\circ\text{C}$ |
| Storage temperature                   | $T_{stg}$ | -55 to +150              | $^\circ\text{C}$ |

Note) \*: Non-repetitive peak collector current

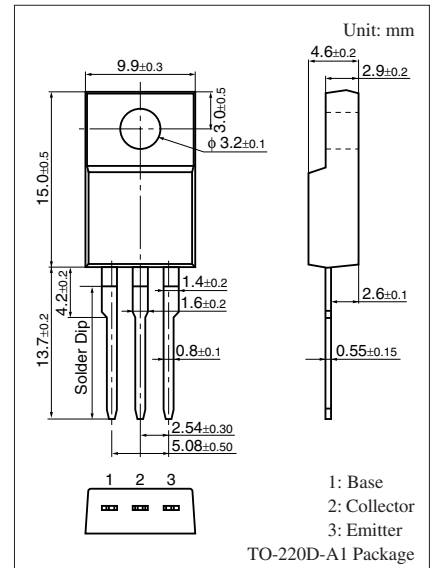
### ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter                                    | Symbol        | Conditions                                                    | Min                    | Typ  | Max  | Unit          |
|----------------------------------------------|---------------|---------------------------------------------------------------|------------------------|------|------|---------------|
| Collector-emitter voltage (Base open)        | $V_{CEO}$     | $I_C = 10\text{ mA}, I_B = 0$                                 | 60                     |      |      | V             |
| Collector-base cutoff current (Emitter open) | $I_{CBO}$     | $V_{CB} = 60\text{ V}, I_E = 0$                               |                        |      | 100  | $\mu\text{A}$ |
| Collector-emitter cutoff current (Base open) | $I_{CEO}$     | $V_{CE} = 60\text{ V}, I_B = 0$                               |                        |      | 100  | $\mu\text{A}$ |
| Emitter-base cutoff current (Collector open) | $I_{EBO}$     | $V_{EB} = 6\text{ V}, I_C = 0$                                |                        |      | 1    | mA            |
| Forward current transfer ratio               | $h_{FE1}$ *   | $V_{CE} = 4\text{ V}, I_C = 1\text{ A}$                       | 120                    |      | 320  | —             |
|                                              | $h_{FE2}$     | $V_{CE} = 4\text{ V}, I_C = 3\text{ A}$                       | 40                     |      |      |               |
| Collector-emitter saturation voltage         | $V_{CE(sat)}$ | $I_C = 3\text{ A}, I_B = 0.375\text{ A}$                      |                        |      | 0.5  | V             |
| Transition frequency                         | $f_T$         | $V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}, f = 10\text{ MHz}$ |                        | 180  |      | MHz           |
| Turn-on time                                 | $t_{on}$      | $I_C = 1\text{ A}, \text{Resistance loaded}$                  |                        | 0.2  | 0.3  | $\mu\text{s}$ |
| Storage time                                 | $t_{stg}$     | $I_{B1} = 0.1\text{ A}, I_{B2} = -0.1\text{ A}$               |                        | 0.55 | 0.70 | $\mu\text{s}$ |
| Fall time                                    | $t_f$         |                                                               | $V_{CC} = 50\text{ V}$ |      | 0.10 | 0.15          |

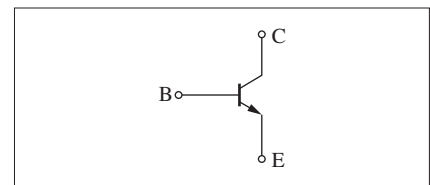
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

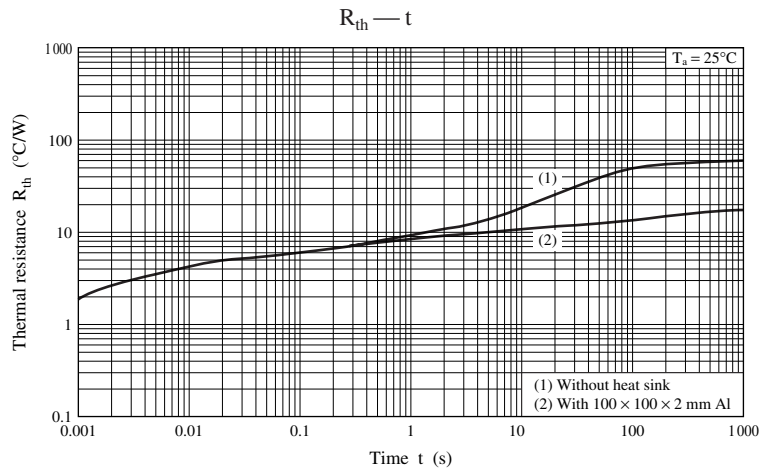
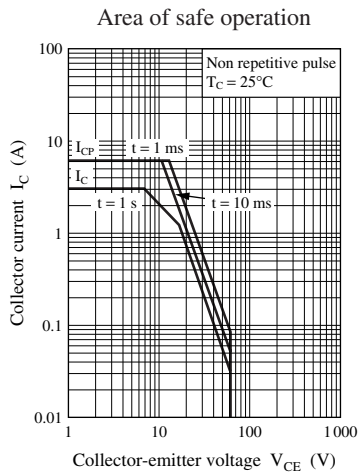
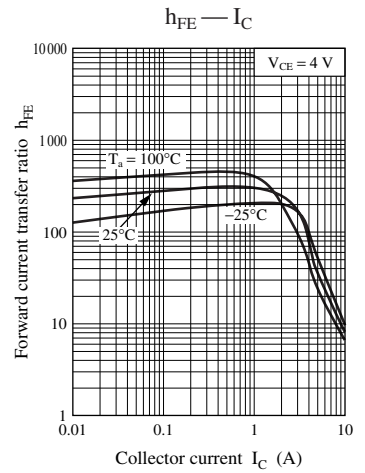
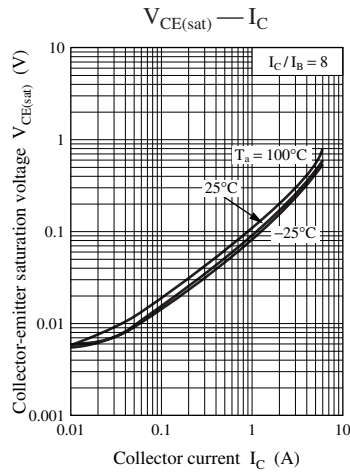
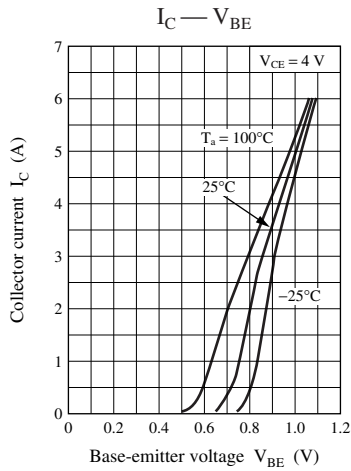
2. \*: Rank classification

| Rank      | Q          | P          |
|-----------|------------|------------|
| $h_{FE1}$ | 120 to 250 | 160 to 320 |



### Internal Connection





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